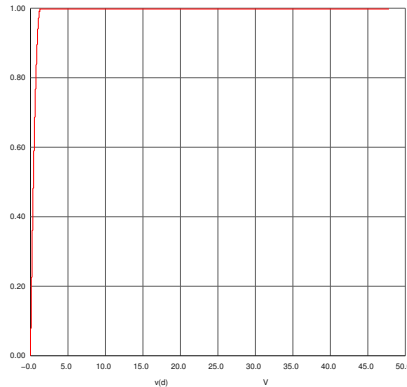


# 1 NMOS Output Characteristics

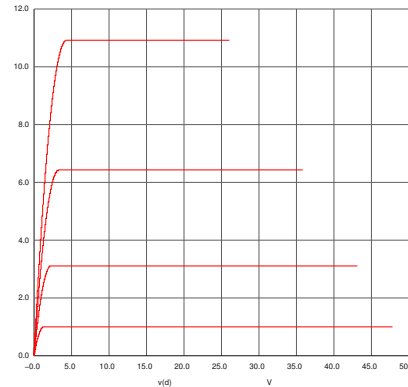
## 1.1 Plots

dc1: param rathour (190070049), ngspice simulation of mosfet circuits  
mA

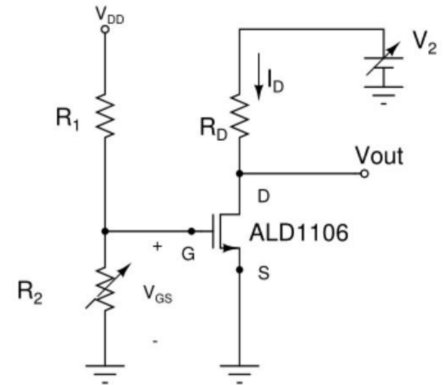


(a)  $I_D$  vs  $V_{DS}$  (for  $V_{GS} = 2V$ )

dc5: param rathour (190070049), ngspice simulation of mosfet circuits  
mA



(b)  $I_D$  vs  $V_{DS}$  (for  $V_{GS} = 2V, 3V, 4V$  &  $5V$ )



(c) BJT current source

## 1.2 Code

To get  $I_D = 1mA$ ,  $K_P = \mu_n \cdot C_{ox} = 1.1834319 \cdot 10^{-4} A/V^2$  (using  $I_d = \frac{W}{2L} K_p (V_{GS} - V_{th})^2$ )

### 1.2.1 $V_{GS} = 2$

```
Param Rathour (190070049), NGSPICE Simulation of MOSFET Circuits
.model NXYAA5U nmos Level=1 Vto=0.7 KP=118.34u w=10u L=1u
+ Gamma=0 Phi=0.65 Lambda=0.0
M1 d g gnd gnd NXYAA5U
VDD Vdd gnd 10 ; Supply Voltage
V2 V2 gnd 5
Vdum V2 Vdum 0
R1 Vdd g 2.2k ; Resistor
R2 g gnd 550 ; Resistor
RD d Vdum 2.2k ; Resistor
.dc V2 0 50 0.01 ; DC Analysis
.control ; Control Functions
run
plot I(Vdum) vs V(d)
.endc
.end
```

### 1.2.2 All $V_{GS}$ values (only changes)

I directly changed  $V_{GS}$  value, as the resistance  $R_2$  doesn't vary linearly. So, dc analysis with  $R_2$  step was not possible. Remove  $R_1$ ,  $R_2$ ,  $V_{dd}$  and dc analysis from previous code and add below lines

```
VGS g gnd 2
.dc V2 0 50 0.01 VGS 2 5 1 ; DC Analysis
```

## 1.3 Learnings

As  $V_{GS}$  increases,  $I_D$  (saturated) increases

As  $V_{GS}$  increases,  $V_{GS}$  (threshold) also increases

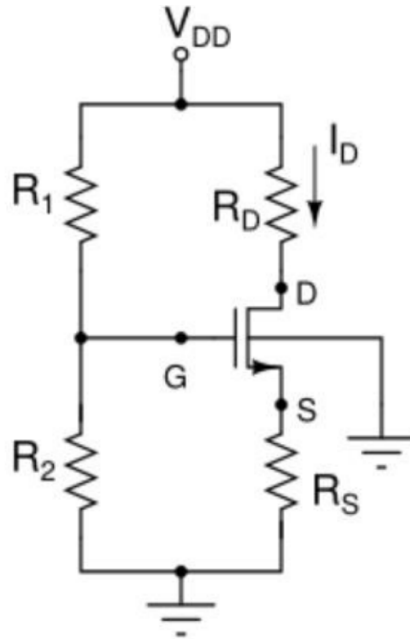
Understood the overall output characteristics of an NMOS transistor and the dependence of  $I_D$  on  $V_{GS}$  and  $V_{DS}$

## 2 Common-Source Amplifier

### 2.1 NMOS Common-Source Amplifier (Bias Circuit)

#### 2.1.1 NGSPICE Values

$V_G = 3.443478V$ ,  $V_D = 8.643329V$ ,  $V_S = 1.017173V$ ,  $I_D = 1.017173 \cdot 10^{-3}mA$



(a) Bias Circuit

#### 2.1.2 Code

```
Param Rathour (190070049), Common-Source Amplifier (Bias Circuit)

.model NXYAA5U nmos Level=1 Vto=1 KP=100u w=10u L=1u
+ Gamma=0 Phi=0.65 Lambda=0.0

M1 d g s gnd NXYAA5U
VDD Vdd gnd 12 ; Supply Voltage
Vdum Vdd Vdum 0

R1 Vdd g 8.2k ; Resistor
R2 g gnd 3.3k ; Resistor
RD d Vdum 3.3k ; Resistor
RS s gnd 1k ; Resistor

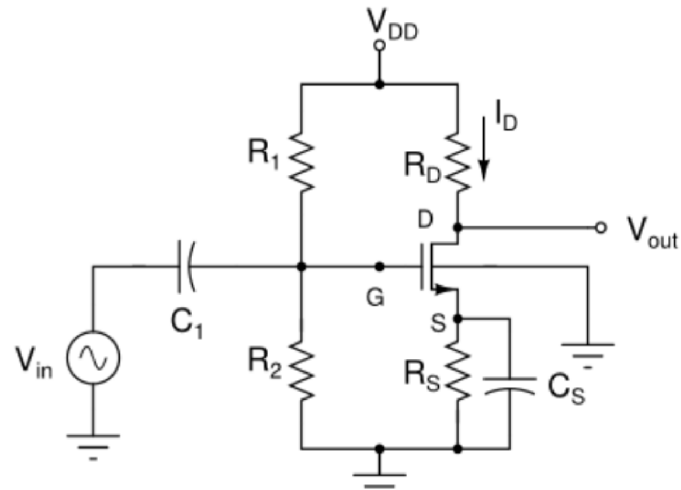
.op ; Operating Point Analysis
.control ; Control Functions
run
print v(g) v(d) v(s) I(Vdum)
.endc
.end
```

#### 2.1.3 Learnings

Analysis Values are close to Simulation values.

Understood the biasing of an NMOS Common-Source amplifier.

## 2.2 NMOS Common-Source Amplifier



(a) Common-Source Amplifier

### 2.2.1 Analysis

$$g_m = \sqrt{2\mu_n C_{ox} \frac{W}{L} I_D} = 1.41\text{U}, \text{ Gain} = -g_m \cdot (R_D \parallel r_o) = -4.5\text{V/V}$$

### 2.2.2 NGSPICE Values

Midband voltage Gain  $\approx -4.76392\text{V/V}$

### 2.2.3 Code

```
Param Rathour (190070049), Common-Source Amplifier
.model NXYAA5U nmos Level=1 Vto=1 KP=100u w=10u L=1u
+ Gamma=0 Phi=0.65 Lambda=0.01
M1 d g s gnd NXYAA5U
VDD Vdd gnd 12 ; Supply Voltage
Vdum Vdd Vdum 0
Vin in gnd sin(0 50m 1000 0 0) ; Input Voltage
R1 Vdd g 8.2k ; Resistor
R2 g gnd 3.3k ; Resistor
RD d Vdum 3.3k ; Resistor
RS s gnd 1k ; Resistor
C1 g in 10u ; Capacitor
CS s gnd 100u ; Capacitor
.tran 0.001m 10m ; Transient Analysis
.control ; Control Functions
run
plot v(d)
meas trans V01 avg v(d) ; Finds DC op value
meas trans V01pp max v(d)
meas trans Vinpp max v(in)
let Gain = (V01pp-V01) / Vinpp
print Gain
.endc
.end
```

### 2.2.4 Learnings

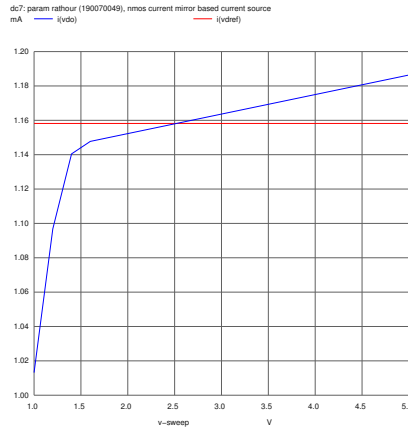
Analysis Values are close to Simulation values.

Understood the performance of an NMOS Common-Source amplifier.

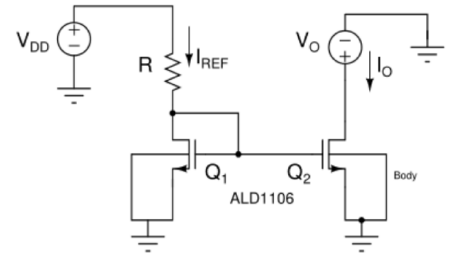
### 3 NMOS Current Mirror based Current Source

Index	v-sweep	i(vdref)	i(vdo)
0	1.000000e+00	1.158142e-03	1.013268e-03
1	1.200000e+00	1.158142e-03	1.096890e-03
2	1.400000e+00	1.158142e-03	1.140274e-03
3	1.600000e+00	1.158142e-03	1.147937e-03
4	1.800000e+00	1.158142e-03	1.150196e-03
5	2.000000e+00	1.158142e-03	1.152456e-03
6	2.200000e+00	1.158142e-03	1.154716e-03
7	2.400000e+00	1.158142e-03	1.156976e-03
8	2.600000e+00	1.158142e-03	1.159235e-03
9	2.800000e+00	1.158142e-03	1.161495e-03
10	3.000000e+00	1.158142e-03	1.163755e-03
11	3.200000e+00	1.158142e-03	1.166014e-03
12	3.400000e+00	1.158142e-03	1.168274e-03
13	3.600000e+00	1.158142e-03	1.170534e-03
14	3.800000e+00	1.158142e-03	1.172794e-03
15	4.000000e+00	1.158142e-03	1.175053e-03
16	4.200000e+00	1.158142e-03	1.177313e-03
17	4.400000e+00	1.158142e-03	1.179573e-03
18	4.600000e+00	1.158142e-03	1.181832e-03
19	4.800000e+00	1.158142e-03	1.184092e-03
20	5.000000e+00	1.158142e-03	1.186352e-03

(a) NGSPICE Values



(b)  $I_{ref}$  and  $I_O$



(c) Current Mirror based Current Source

#### 3.1 Analysis

$$I_D = \frac{W}{2L} K_p (V_{GS} - V_{th})^2 = 1.15mA$$

$$I_O = I_{ref} \left( 1 + \frac{V_O - V_{GS}}{V_A} \right) = 1.13mA, 1.14mA, 1.15mA, 1.16mA, 1.17mA \text{ for } V_O = 1V, 2V, 3V, 4V, 5V \text{ respectively}$$

#### 3.2 Code

```
Param Rathour (190070049), NMOS Current Mirror based Current Source

.model NXYAA5U nmos Level=1 Vto=1 KP=100u w=10u L=1u
+ Gamma=0 Phi=0.65 Lambda=0.01

M1 d1 d1 gnd gnd NXYAA5U
M2 Vd0 d1 gnd gnd NXYAA5U
VDD Vdd gnd 12 ; Supply Voltage
VdRef Vdd VdRef 0
Vo Vo gnd 1 ; Voltage
Vd0 Vo Vd0 0

R VdRef d1 8.2k ; Resistor

.dc Vo 1 5 0.2 ; DC Analysis
.control ; Control Functions
run
print I(VdRef) I(Vd0)
plot I(VdRef) I(Vd0)
* plot I(Vdd)
* plot I(Vo)
.endc
```

#### 3.3 Learnings

Analysis Values are close to Simulation values.

Understood the design and implementation of a practical current mirror using a general purpose NMOS arrays IC (ALD1106).